

# **R5110x Series**

# **AEC-Q100 Compliant**

# 36V System Power Supply with Watchdog Timer for Automotive Applications

No. EC-326-231121

## **OUTLINE**

R5110x is the system power supply and supervisor IC based on the high-voltage CMOS process technology, and has high accuracy and ultra low supply current voltage.

R5110x consists of a voltage regulator (VR), a voltage detector (VD), and a normal / window type of watchdog timer (WDT) in a chip, and can provide three functions of the system power supply, the supply voltage supervisor, and the supervision of system's miss operation.

Voltage Regulator allows the output current of 500 mA. And, VR has the inrush current protection circuit for rising pulse (Typ.400 mA or less). Voltage Detector outputs a reset signal when a reduction of supply voltage (SENSE / Vout) is detected, and the reset signal is used as system reset. The detection voltage is internally fixed in an IC. And, the delay time is adjustable with an external capacitor because VD has the built-in release delay circuit (the power-on reset circuit). When the supply voltage is higher than the release output voltage, VD maintains the reset state during the delay time. The output type of RESETB and Dout are Nch open-drain. In addition, R5110xxx2C and R5110xxx2D (Detector with SENSE pin) have a manual reset (MR) pin.

Watchdog Timer detects the microprocessor output pulse. In addition to the normal type of WDT (R5110Sxx1A / R5110xxx2C) that outputs a reset signal when the detected pulse period is longer than normal, R5110x supports the window type of WDT (R5110Sxx1B / R5110xxx2D) that outputs a reset signal when the detected pulse period is shorter or longer. RESETB outputs the reset signal when using R5110Sxx1A / R5110Sxx1B, and the WDO pin outputs "L" as the reset signal when using R5110xxx2C / R5110xxx2D. The output type of WDO is Nch open-drain. In addition, R5110xxx2C and R5110xxx2D have an inhibiting (INH) pin to stop the watchdog timer's monitoring function. The time out period of Watchdog Timer is also adjustable with an external capacitor. R5110x supports the packages of HSOP-8E, HSOP-18 and HQFN0808-28.

#### **FEATURES**

Operating	Voltage Range	(Maximum Rating) ······	· 3.5 V to 36.0 V (50.0 V)

● Operating Temperature Range ······ -40°C to 125°C

Supply Current······ Typ. 25 μA

Supply Current (On standby)····· Typ. 0.2 μA

#### <Voltage Regulator (VR)>

Output Voltage Range · .... 1.8 V to 5.0 V

● Dropout Voltage · · · · · · Typ. 0.5 V (Vout = 5.0 V, 500 mA)

Output Voltage Accuracy ····· ±1.5% (-40°C ≤ Ta ≤ 125°C)

Output Voltage Temperature Coefficient ····· Typ. ±100 ppm/°C

Built-in Short Current Limit Circuit · · · · · Typ. 80 mA

Built-in Overcurrent Protection Circuit · · · · · Min. 500 mA

Built-in Thermal Shutdown Circuit ······ Typ.165°C
 Recommended Ceramic Capacitor ···· 0.1 µF or more

#### <Voltage Detector (VD)>

● Detector Threshold Range······ 1.6 V to 5.5 V

Detector Threshold Accuracy ······ ±1.8% (-40°C ≤ Ta ≤ 125°C)

Release Delay Accuracy ····· ±20% (-40°C ≤ Ta ≤ 125°C)

■ Release Delay Time · · · · · · · · · · · · Typ. 242 ms (C<sub>D</sub> = 0.22 μF)

Delay Time is adjustable with an external capacitor.

#### <Watchdog Timer (WDT)>

Open Window Accuracy ······ ±20% (-40°C ≤ Ta ≤ 125°C)

● Open Window Time · · · · · · Typ.18 ms (C<sub>TW</sub> = 10 nF)

● Closed Window Time · Typ.18 ms (C<sub>TW</sub> = 10 nF)

■ Long Open Window Time ······ Typ.72 ms (C<sub>TW</sub> = 10 nF)

● Ignoring Time · · · · · Typ.18 ms (C<sub>TW</sub> = 10 nF)

● Monitoring Time · · · · · Typ.18 ms (C<sub>TW</sub> = 10 nF)

■ Reset Time · Typ.9.5 ms (C<sub>TW</sub> = 10 nF)

Each time is adjustable with an external capacitor.

#### **APPLICATIONS**

- Power source for car accessories including car audio equipment, car navigation system, and ETC system.
- Power source for control units including EV inverter and charge control.

# **SELECTION GUIDE**

R5110x user selectable options (Watchdog Timer type, Detector type, and additional functions with using MR / INH / WDO pins) are as follows:

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R5110Sxx1*-E2-#E	HSOP-8E	1,000 pcs	Yes	Yes
R5110Sxx2*-E2-#E	HSOP-18	1,000 pcs	Yes	Yes
R5110Lxx2*-TR-#E	HQFN0808-28	2,000pcs	Yes	Yes

xx: Specify the set output voltage ( $V_{SET}$ ) and the set detector threshold (- $V_{SET}$ ) by using serial numbers starting from 01.

Refer to "Mark Specification Table" for details.

\*:

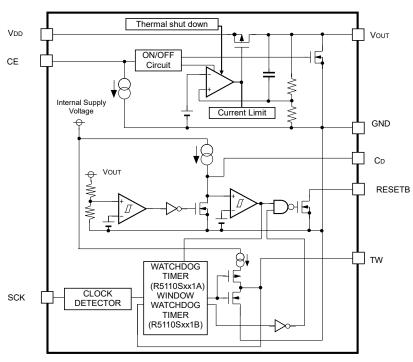
	Detector Monitoring Voltage	Package	Watchdog Timer Type	MR / INH / WDO pins	RESETB/ Dout pins
Α	V <sub>OUT</sub>	HSOP-8E	Normal	_	RESETB
В	Vout	HSOP-8E	Window	-	RESETB
С	SENSE	HSOP-18 HQFN0808-28	Normal	Yes	D <sub>оит</sub>
D	SENSE	HSOP-18 HQFN0808-28	Window	Yes	D <sub>оит</sub>

#### #: Quality Class

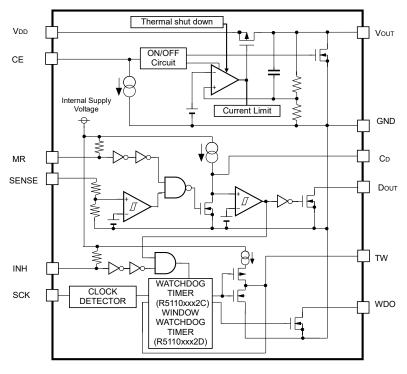
#	Operating Temperature Range	Test Temperature	AEC-Q100
Α	-40°C to 125°C	25°C, High	Grade 1
K	-40°C to 125°C	Low, 25°C, High	Grade 1

# **BLOCK DIAGRAMS**

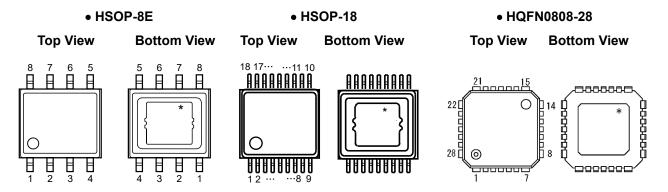
#### R5110Sxx1A / R5110Sxx1B



#### R5110xxx2C / R5110xxx2D



# **PIN DESCRIPTION**



#### **HSOP-8E (R5110Sxx1A / R5110Sxx1B)**

Pin No.	Symbol	Description
1	$V_{DD}$	Supply Voltage pin
2	CE	Chip Enable pin (Active "H")
3	GND	GND pin
4	С	VD Release Delay Time Set pin
5	TW	WDT Monitoring Time Set pin
6	SCK	WDT Pulse Input pin
7	RESETB <sup>(1)</sup>	Reset Output pin (Active "L"), Nch Open Drain Output type
8	V <sub>OUT</sub>	VR Output pin

<sup>\*</sup> The tab on the bottom of the package enhances thermal performance and is electrically connected to GND (substrate level). It is recommended that the tab be connected to the ground plane on the board, or otherwise be left open.

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<sup>(1)</sup> RESETB pin is required to pull up to a suitable voltage with an external resister.

## HSOP-18 (R5110Sxx2C / R5110Sxx2D)

Pin No.	Symbol	Description
1	$V_{DD}$	Supply Voltage pin
2	CE	Chip Enable pin (Active "H")
3	NC	No Connection
4	NC	No Connection
5	GND	GND pin
6	NC	No Connection
7	NC	No Connection
8	C <sub>D</sub>	VD Release Delay Time Set pin
9	MR	Manual Reset pin (Active "L")
10	TW	WDT Monitoring Time Set pin
11	INH	Inhibition pin (Active "L")
12	SCK	WDT Pulse Input pin
13	WDO <sup>(1)</sup>	WDT Output pin, Nch Open Drain Output type
14	D <sub>OUT</sub> <sup>(2)</sup>	Reset Output pin (Active "L"), Nch Open Drain Output type
15	SENSE	VD Voltage SENSE pin
16	NC	No Connection
17	NC	No Connection
18	V <sub>оит</sub>	VR Output pin

<sup>\*</sup> The tab on the bottom of the package enhances thermal performance and is electrically connected to GND (substrate level). It is recommended that the tab be connected to the ground plane on the board, or otherwise be left open.

<sup>&</sup>lt;sup>(1)</sup> WDO pin is required to pull up to a suitable voltage with an external resister.

<sup>(2)</sup> Dout pin is required to pull up to a suitable voltage with an external resister.

## HQFN0808-28 (R5110Lxx2C / R5110Lxx2D)

Pin No.	Symbol	Description
1	GND	GND pin
2	NC	No Connection
3	$V_{DD}$	Supply Voltage pin
4	NC	No Connection
5	CE	Chip Enable pin (Active "H")
6	NC	No Connection
7	GND	GND pin
8	GND	GND pin
9	GND	GND pin
10	С	VD Release Delay Time Set pin
11	MR	Manual Reset pin (Active "L")
12	TW	WDT Monitoring Time Set pin
13	INH	Inhibition pin (Active "L")
14	GND	GND pin
15	GND	GND pin
16	SCK	WDT Pulse Input pin
17	NC	No Connection
18	WDO <sup>(1)</sup>	WDT Output pin, Nch Open Drain Output type
19	D <sub>OUT</sub> (2)	Reset Output pin (Active "L"), Nch Open Drain Output type
20	SENSE	VD Voltage SENSE pin
21	GND	GND pin
22	GND	GND pin
23	NC	No Connection
24	NC	No Connection
25	NC	No Connection
26	V <sub>out</sub>	VR Output pin
27	NC	No Connection
28	GND	GND pin

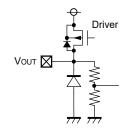
<sup>\*</sup> The tab on the bottom of the package enhances thermal performance and is electrically connected to GND (substrate level). It is recommended that the tab be connected to the ground plane on the board, or otherwise be left open.

<sup>&</sup>lt;sup>(1)</sup> WDO pin is required to pull up to a suitable voltage with an external resister.

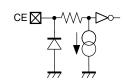
<sup>(2)</sup> DOUT pin is required to pull up to a suitable voltage with an external resister.

#### PIN EQUIVALENT CIRCUIT DIAGRAMS

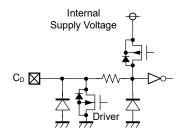
<Vour pin>



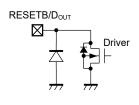
<CE pin>



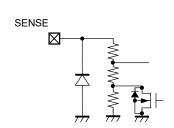
#### <C<sub>D</sub> pin>



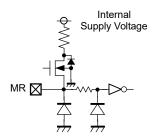
<RESETB pin(R5110Sxx1x) / Dout pin(R5110xxx2x)>



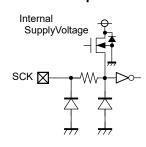
## <SENSE pin (R5110xxx2x)>



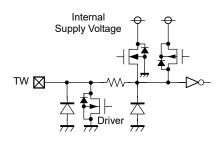
#### <MR pin (R5110xxx2x)>



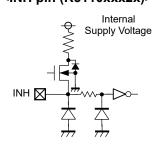
## <SCK pin>



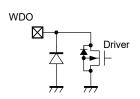
## <TW pin>



## <INH pin (R5110xxx2x)>



## <WDO pin (R5110xxx2x)>



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol		Item	Rating	Unit	
Vin	Input Voltage		-0.3 to 50	V	
	Peak Voltage <sup>(1)</sup>		60	V	
Vce	CE Pin Input Voltage -0.3 to 50				
V <sub>OUT</sub>	Output Voltage		$-0.3$ to $V_{IN} + 0.3 \le 50$	V	
$V_{CD}$	C <sub>D</sub> Pin Output `	/oltage	-0.3 to 7.0	V	
$V_{TW}$	TW Pin Output	Voltage	-0.3 to 7.0	V	
VRESETB	RESETB Pin C	output Voltage	-0.3 to 7.0	V	
V <sub>DOUT</sub>	Douт Pin Outpu	ıt Voltage	-0.3 to 7.0	V	
$V_{WDO}$	WDO Pin Outp	ut Voltage	-0.3 to 7.0	V	
Vsck	SCK Pin Input	Voltage	-0.3 to 7.0	V	
VINH	INH Pin Input \	/oltage	-0.3 to 7.0	V	
V <sub>MR</sub>	MR Pin Input V	'oltage	-0.3 to 7.0	V	
VSENSE	SENSE Pin Inp	out Voltage	-0.3 to 7.0	V	
	Dower	HSOP-8E (JEDEC STD.51)	3600		
$P_D$	Power Dissipation (2)	HSOP-18 (JEDEC STD.51)	3900	mW	
	Dissipation (=)	HQFN0808-28 (JEDEC STD.51)	5800		
Tj	Junction Temp	erature	-40 to 150	°C	
Tstg	Storage Tempe	erature	−55 to 150	°C	

#### **ABSOLUTE MAXIMUM RATINGS**

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Rating	Unit
V <sub>IN</sub>	Input Voltage	3.5 to 36.0	V
Vce	CE Pin Input Voltage	0 to 36.0	V
V <sub>SCK</sub>	SCK Pin Input Voltage	0 to 5.5	V
V <sub>INH</sub>	INH Pin Input Voltage	0 to 5.5	V
V <sub>MR</sub>	MR Pin Input Voltage	0 to 5.5	V
Vsense	SENSE Pin Input Voltage	0 to 5.5	V
Та	Operating Temperature Range	-40 to 125	°C

#### **RECOMMENDED OPERATING CONDITONS**

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such ratings by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

<sup>(1)</sup> Within application time of 200 ms

<sup>(2)</sup> Refer to POWER DISSIPATION for detailed information.

# **ELECTRICAL CHARACTERISTICS**

 $C_{IN}$  =  $C_{OUT}$  = 0.1 $\mu$ F,  $V_{IN}$  = 14 V, unless otherwise noted.

The specification in \_\_\_ is checked and guaranteed by design engineering at −40°C ≤ Ta ≤ 125°C.

R5110xxxxx-AE (Ta = 25°C)

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
I <sub>SS</sub>	Supply Current	I <sub>OUT</sub> = 0 mA		25	38	μA
Istandby	Power Consumption (on standby)	V <sub>IN</sub> = 36 V, V <sub>CE</sub> = 0 V		0.2	4.0	μA
I	CE Pull-downConstant Current	VCE = 5 V		0.2	0.6	μA
I <sub>PD</sub>		VCE = 36 V		0.5	1.3	μA
V <sub>CEH</sub>	CE Input Voltage «H»		2.2		36	V
VCEL	CE Input Voltage «L»				1.0	V

VR Part  $(Ta = 25^{\circ}C)$ 

Symbol	Item	Conditi	ons	Min.	Тур.	Max.	Unit
V <sub>OUT</sub>	Output Voltage	I <sub>OUT</sub> = 1 mA		×0.985		×1.015	V
ΔVουτ/ΔΙουτ	Load Regulation			-20	0	30	mV
			V <sub>SET</sub> = 1.8		1.70	1.90	V
V <sub>DIF</sub>	Dropout Voltage	Jan = 500m A	V <sub>SET</sub> = 2.5		1.00	1.55	V
		10UT - 500MA	V <sub>SET</sub> = 3.3		0.60	1.20	٧
			V <sub>SET</sub> = 5.0		0.50	0.95	V
$\Delta V_{OUT}/\Delta V_{IN}$	Line Regulation	$3.5V \le V_{SET} + 0.5$ I <sub>OUT</sub> = 1 mA	V ≤ V <sub>IN</sub> ≤ 36V		0.01	0.02	%/V
ILIM	Output Current Limit	V <sub>IN</sub> = V <sub>SET</sub> + 3.0 V	,	500	750	1000	mA
Isc	Short current Limit	V <sub>IN</sub> = 5 V, V <sub>OUT</sub> =	0 V	35	80	135	mA
T <sub>TSD</sub>	Thermal Shutdown Temperature		150	165		°C	
T <sub>TSR</sub>	Thermal Shutdown Release Temperature	$3.5V \le V_{SET} + 0.5V \le V_{IN} \le 36V$ $I_{OUT} = 1 \text{ mA}$ $V_{IN} = V_{SET} + 3.0 \text{ V}$ $V_{IN} = 5 \text{ V}, V_{OUT} = 0 \text{ V}$ $J_{UN} = 5 \text{ V}, V_{OUT} = 0 \text{ V}$	140		°C		
R <sub>Low</sub>	V <sub>OUT</sub> Low Output Nch Tr.ON Resistance	$V_{IN} = V_{SET} + 2.0 \text{ V} $ $I_{IDM} \leq I_{OUT} \leq 500 \text{ mA}$ $V_{SET} = 1.8$ $V_{SET} = 2.5$ $V_{SET} = 3.3$ $V_{SET} = 3.3$ $V_{SET} = 5.0$ $I_{OUT} = 1 \text{ mA}$ $I_{IDM} =$	kΩ				

 $C_{\text{IN}}$  =  $C_{\text{OUT}}$  = 0.1  $\mu\text{F}$ ,  $V_{\text{IN}}$  = 14 V, unless otherwise noted. The specification in  $\square$  is checked and guaranteed by design engineering at  $-40^{\circ}\text{C} \le \text{Ta} \le 125^{\circ}\text{C}$ .

VD Part (Ta = 25°C)

Symbol	ltem	Conditions	Min.	Тур.	Max.	Unit
-V <sub>DET</sub>	Detector Threshold	V <sub>OUT</sub> Set Detector Threshold	x0.982		x1.018	V
V <sub>HYS</sub>	Detector Threshold Hysteresis		(-V <sub>DET</sub> ) x0.01	(-V <sub>DET</sub> ) x0.02	(-V <sub>DET</sub> ) x0.03	٧
tdelay	Release Output Delay Time (Power-On Reset)	C <sub>D</sub> = 0.22 μF	194	242	290	ms
$V_{RESETB}$	RESETB Pull-up Voltage	R5110Sxx1A / R5110Sxx1B			5.5	V
V <sub>DOUT</sub>	Do∪⊤ Pull-up Voltage	R5110xxx2C / R5110xxx2D			5.5	V
I <sub>OUTNRSTB</sub>	Nch. Output Current (RESETB Output Pin)	R5110Sxx1A / R5110Sxx1B V <sub>IN</sub> = 3.5 V, V <sub>RESETB</sub> = 0.1 V	0.7	1.5		mA
ILEAKRSTB	Nch. Leakage Current (RESETB Output Pin)	R5110Sxx1A / R5110Sxx1B V <sub>RESETB</sub> = 5.5 V			0.3	μΑ
Іоитроит	Nch. Output Current (Doυτ Output Pin)	R5110xxx2C / R5110xxx2D V <sub>IN</sub> = 3.5 V, V <sub>DOUT</sub> = 0.1 V	0.7	1.5		mA
I <sub>LEAKDOUT</sub>	Nch. Leakage Current (Dουτ Output Pin)	R5110xxx2C / R5110xxx2D V <sub>DOUT</sub> = 5.5 V			0.3	μΑ
$V_{MRH}$	MR Input "H"		1.5		5.5	V
V <sub>MRL</sub>	MR Input "L"		0		0.6	V
MRW	MR Input Pulse Width		2			μs
RMR	MR Pull-up Resistance		50	110	160	kΩ
RLCD	C <sub>D</sub> Pin Discharge	V <sub>CE</sub> = 0 V, V <sub>CD</sub> = 0.1 V		7.5	20	kΩ
INLOD	Nch Tr.ON Resistance	VCE		7.5	20	11.5.2

 $C_{\text{IN}}$  =  $C_{\text{OUT}}$  = 0.1 $\mu$ F,  $V_{\text{IN}}$  = 14 V, unless otherwise noted. The specification in  $\square$  is checked and guaranteed by design engineering at  $-40^{\circ}\text{C} \le \text{Ta} \le 125^{\circ}\text{C}$ .

WDT Part  $(Ta = 25^{\circ}C)$ 

Symbol	Item	Condi	tions	Min.	Тур.	Max.	Unit
tow	Open Window Time			14.4	18.0	21.6	ms
tcw	Closed Window Time	R5110Sxx1B/ R5110xxx2D	C <sub>TW</sub> = 10 nF	14.4	18.0	21.6	ms
towL	Long Open Window Time	NOTTOXXXZD		36.0	72.0	108.0	ms
t <sub>IGN</sub>	Ignoring Time	C <sub>TW</sub> = 10 nF		14.4	18.0	21.6	ms
t <sub>WD</sub>	Monitoring Time	R5110Sxx1A/ R5110xxx2C	C <sub>TW</sub> = 10 nF	14.4	18.0	21.6	ms
twR	Reset Time	C <sub>TW</sub> = 10 nF		7.6	9.5	11.4	ms
Vsckh	SCK Input "H"			1.5		5.5	V
Vsckl	SCK Input "L"			O		0.65	V
VINHH	INH Input "H"			1.5		5.5	V
VINHL	INH Input "L"			O		0.6	V
Rinh	INH Pull-up Resistance			50	110	160	kΩ
tsckwh	SCK Minimum Input Pulse Width "H"	V <sub>SCKL</sub> = 0.5, V <sub>SC</sub>	скн = 1.6	500			ns
tsckwl	SCK Minimum Input Pulse Width "L"	V <sub>SCKL</sub> = 0.5, V <sub>SC</sub>	скн = 1.6	1500			ns
$V_{\text{WDO}}$	WDO Pull-up Voltage					5.5	V
louтnwdo	Nch. Output Current (WDO Output Pin)	R5110xxx2C / R5110xxx2D V <sub>IN</sub> = 3.5 V, V <sub>DS</sub> = 0.1 V		0.7	1.5		mA
I <sub>LEAKWDO</sub>	Nch. Leakage Current (WDO Output Pin)	R5110xxx2C / R5110xxx2D VwDo = 5.5 V				0.3	μA
R <sub>LTW</sub>	C <sub>TW</sub> Discharge Nch Tr.ON Resistance	$V_{CE} = 0 \text{ V}, V_{CTW} = 0.1 \text{ V}$			7.5	20	kΩ

All test items listed under Electrical Characteristics are done under the pulse load condition ( $Tj \approx Ta = 25$ °C).

## **Product-specific Electrical Characteristics**

The specification in  $\square$  is checked and guaranteed by design engineering at  $-40^{\circ}\text{C} \le \text{Ta} \le 125^{\circ}\text{C}$ .

## **R5110xxxxx-AE Product-specific Electrical Characteristics**

VR Part  $(Ta = 25^{\circ}C)$ 

Product Name		V <sub>OUT</sub> [V]	V <sub>DIF</sub> [V]		
Product Name	Min.	Тур.	Max.	Тур.	Max.
R5110x01xx	4.925	5.000	5.075	0.50	0.95
R5110x02xx	1.773	1.800	1.827	1.70	1.90
R5110x03xx	4.925	5.000	5.075	0.50	0.95
R5110x04xx	4.925	5.000	5.075	0.50	0.95
R5110x05xx	4.925	5.000	5.075	0.50	0.95
R5110x06xx	4.925	5.000	5.075	0.50	0.95
R5110x07xx	4.925	5.000	5.075	0.50	0.95
R5110x08xx	3.251	3.300	3.349	0.60	1.20
R5110x09xx	3.251	3.300	3.349	0.60	1.20
R5110x10xx	3.251	3.300	3.349	0.60	1.20
R5110x11xx	3.251	3.300	3.349	0.60	1.20
R5110x12xx	4.925	5.000	5.075	0.50	0.95
R5110x13xx	3.349	3.400	3.451	0.60	1.20
R5110x142x	3.251	3.300	3.349	0.60	1.20

**VD Part** (Ta =  $25^{\circ}$ C)

Product Name	-V <sub>DET</sub> [V]			V <sub>HYS</sub> [V]			
Product Name	Min.	Тур.	Max.	Min.	Тур.	Max.	
R5110x01xx	4.518	4.600	4.682	0.046	0.092	0.138	
R5110x02xx	1.572	1.600	1.628	0.016	0.032	0.048	
R5110x03xx	4.419	4.500	4.581	0.045	0.090	0.135	
R5110x04xx	4.321	4.400	4.479	0.044	0.088	0.132	
R5110x05xx	4.223	4.300	4.377	0.043	0.086	0.129	
R5110x06xx	4.125	4.200	4.275	0.042	0.084	0.126	
R5110x07xx	3.634	3.700	3.766	0.037	0.074	0.111	
R5110x08xx	2.946	3.000	3.054	0.030	0.060	0.090	
R5110x09xx	2.848	2.900	2.952	0.029	0.058	0.087	
R5110x10xx	2.750	2.800	2.850	0.028	0.056	0.084	
R5110x11xx	2.652	2.700	2.748	0.027	0.054	0.081	
R5110x12xx	4.027	4.100	4.173	0.041	0.082	0.123	
R5110x13xx	3.045	3.100	3.155	0.031	0.062	0.093	
R5110x142x	4.518	4.600	4.682	0.046	0.092	0.138	

 $C_{IN}$  =  $C_{OUT}$  = 0.1 $\mu$ F,  $V_{IN}$  = 14 V, unless otherwise noted.

**R5110xxxxx-KE** (−40°C ≤ Ta ≤ 125°C)

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Iss	Supply Current	I <sub>OUT</sub> = 0 mA		25	38	μA
Istandby	Power Consumption (on standby)	V <sub>IN</sub> = 36 V,V <sub>CE</sub> = 0 V		0.2	4.0	μA
l	CE Pull-down Constant	VCE = 5 V		0.2	0.6	μA
I <sub>PD</sub>	Current	VCE = 36 V		0.5	1.3	μΑ
V <sub>CEH</sub>	CE Input Voltage «H»		2.2		36	V
VCEL	CE Input Voltage «L»				1.0	V

VR Part  $(-40^{\circ}\text{C} \le \text{Ta} \le 125^{\circ}\text{C})$ 

Symbol	Item	Conditions		Min.	Тур.	Max.	Unit
Vout	Output Voltage	I <sub>OUT</sub> =1 mA		×0.985		×1.015	V
ΔVουτ/ΔΙουτ	Load Regulation	$V_{IN} = V_{SET} + 2.0 \text{ V}$ $1\text{mA} \le I_{OUT} \le 500 \text{ mA}$		-20	0	30	mV
			V <sub>SET</sub> = 1.8		1.70	1.90	V
$V_DIF$	Dropout Voltage	I <sub>OUT</sub> = 500mA	V <sub>SET</sub> = 2.5		1.00	1.55	V
<b>V</b> DIF	Dropout Voltage	IOUT - SOUTHA	V <sub>SET</sub> = 3.3		0.60	1.20	V
			V <sub>SET</sub> = 5.0		0.50	0.95	V
$\Delta V_{OUT}/\Delta V_{IN}$	Line Regulation	$3.5V \le V_{SET} + 0.5V \le V_{IN} \le 36V$ $I_{OUT} = 1 \text{ mA}$			0.01	0.02	%/V
ILIM	Output Current Limit	V <sub>IN</sub> = V <sub>SET</sub> + 3.0 V		500	750	1000	mA
Isc	Short current Limit	V <sub>IN</sub> = 5 V, V <sub>OUT</sub> = 0 V		35	80	135	mA
T <sub>TSD</sub>	Thermal Shutdown Temperature	Junction Temperature		150	165		°C
T <sub>TSR</sub>	Thermal Shutdown Release Temperature	Junction Temperature		125	140		°C
R <sub>LOW</sub>	V <sub>ОUТ</sub> Low Output Nch Tr.ON Resistance	V <sub>CE</sub> = 0 V, V <sub>OUT</sub> = 0.1 V			3.2	7.0	kΩ

 $C_{\text{IN}}$  =  $C_{\text{OUT}}$  = 0.1  $\mu\text{F},~V_{\text{IN}}$  = 14 V, unless otherwise noted.

**VD Part** (−40°C ≤ Ta ≤ 125°C)

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
-V <sub>DET</sub>	Detector Threshold	V <sub>OUT</sub> Set Detector Threshold	x0.982		x1.018	V
V <sub>HYS</sub>	Detector Threshold Hysteresis		(-V <sub>DET</sub> ) x0.01	(-V <sub>DET</sub> ) x0.02	(-V <sub>DET</sub> ) x0.03	V
tdelay	Release Output Delay Time (Power-On Reset)	C <sub>D</sub> = 0.22 μF	194	242	290	ms
V <sub>RESETB</sub>	RESETB Pull-up Voltage	R5110Sxx1A / R5110Sxx1B			5.5	V
V <sub>DOUT</sub>	D <sub>о∪т</sub> Pull-up Voltage	R5110xxx2C / R5110xxx2D			5.5	V
loutnrstb	Output Current (RESETB Output Pin)	R5110Sxx1A / R5110Sxx1B Nch, V <sub>DD</sub> = 3.5 V, V <sub>DS</sub> = 0.1 V	0.7	1.5		mA
ILEAKRSTB	Nch Leakage Current (RESETB Output Pin)	R5110Sxx1A / R5110Sxx1B V <sub>RESETB</sub> = 5.5 V			0.3	μA
Іоитроит	Output Current (Dout Output Pin)	R5110xxx2C / R5110xxx2D Nch, V <sub>DD</sub> = 3.5 V, V <sub>DS</sub> = 0.1 V	0.7	1.5		mA
I <sub>LEAKDOUT</sub>	Nch Leakage Current (Dout Output Pin)	R5110xxx2C / R5110xxx2D V <sub>DOUT</sub> = 5.5 V			0.3	μΑ
$V_{MRH}$	MR Input "H"		1.5		5.5	V
V <sub>MRL</sub>	MR Input "L"		0		0.6	V
MRW	MR Input Pulse Width		2			μs
RMR	MR Pull-up Resistance		50	110	160	kΩ
R <sub>LCD</sub>	C <sub>D</sub> Pin Discharge Nch Tr.ON Resistance	V <sub>CE</sub> = 0 V, V <sub>CD</sub> = 0.1 V		7.5	20	kΩ

 $C_{\text{IN}}$  =  $C_{\text{OUT}}$  = 0.1  $\mu\text{F},~V_{\text{IN}}$  = 14 V, unless otherwise noted.

**WDT Part** (−40°C ≤ Ta ≤ 125°C)

Symbol	Item	Cond	litions	Min.	Тур.	Max.	Unit
tow	Open Window Time	Jone		14.4	18.0	21.6	ms
	•	R5110Sxx1B/					
tcw	Closed Window Time	R5110xxx2D	C <sub>TW</sub> = 10 nF	14.4	18.0	21.6	ms
towL	Long Open Window Time			36.0	72.0	108.0	ms
t <sub>IGN</sub>	Ignoring Time	C <sub>TW</sub> = 10 nF		14.4	18.0	21.6	ms
t <sub>WD</sub>	Monitoring Time	R5110Sxx1A/ R5110xxx2C	C <sub>TW</sub> = 10 nF	14.4	18.0	21.6	ms
$t_{WR}$	Reset Time	C <sub>TW</sub> = 10 nF		7.6	9.5	11.4	ms
Vsckh	SCK Input "H"			1.5		5.5	V
Vsckl	SCK Input "L"			0		0.65	V
VINHH	INH Input "H"			1.5		5.5	V
VINHL	INH Input "L"					0.6	V
RINH	INH Pull-up Resistance			50	110	160	kΩ
tsскwн	SCK Minimum Input Pulse Width "H"	V <sub>SCKL</sub> =0.5, V <sub>SC</sub>	кн =1.6	500			ns
tsckwl	SCK Minimum Input Pulse Width "L"	V <sub>SCKL</sub> =0.5, V <sub>SC</sub>	жн =1.6	1500			ns
$V_{\text{WDO}}$	WDO Pull-up Voltage					5.5	V
I <sub>OUTNWDO</sub>	Output Current (WDO Output Pin)	R5110xxx2C / R5110xxx2D V <sub>DD</sub> = 3.5 V, V <sub>DS</sub> = 0.1 V		0.7	1.5		mA
ILEAKWDO	Nch Leakage Current (WDO Output Pin)	R5110xxx2C / R5110xxx2D Vwpo = 5.5 V				0.3	μA
D	C <sub>TW</sub> Discharge				7.5	20	kΩ
KLIW	R <sub>LTW</sub> Nch Tr.ON Resistance		$V_{CE} = 0 \text{ V}, V_{CTW} = 0.1 \text{ V}$		7.5	20	K22

#### **Product-specific Electrical Characteristics**

# R5110xxxxx-KE Product-specific Electrical Characteristics VR Part

(-40°C ≤ Ta ≤ 125°C)

Product Name		V <sub>OUT</sub> [V]		V <sub>DIF</sub>	= [V]
Product Name	Min.	Тур.	Max.	Тур.	Max.
R5110x01xx	4.925	5.000	5.075	0.50	0.95
R5110x02xx	1.773	1.800	1.827	1.70	1.90
R5110x03xx	4.925	5.000	5.075	0.50	0.95
R5110x04xx	4.925	5.000	5.075	0.50	0.95
R5110x05xx	4.925	5.000	5.075	0.50	0.95
R5110x06xx	4.925	5.000	5.075	0.50	0.95
R5110x07xx	4.925	5.000	5.075	0.50	0.95
R5110x08xx	3.251	3.300	3.349	0.60	1.20
R5110x09xx	3.251	3.300	3.349	0.60	1.20
R5110x10xx	3.251	3.300	3.349	0.60	1.20
R5110x11xx	3.251	3.300	3.349	0.60	1.20
R5110x12xx	4.925	5.000	5.075	0.50	0.95
R5110x13xx	3.349	3.400	3.451	0.60	1.20
R5110x142x	3.251	3.300	3.349	0.60	1.20

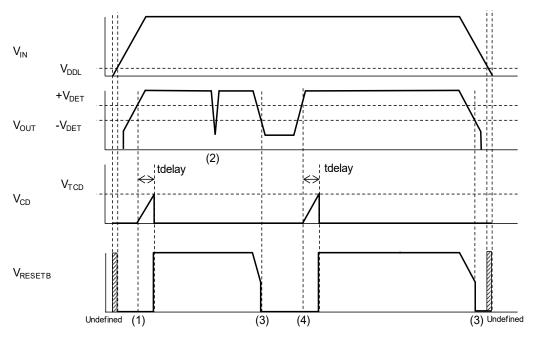
**VD Part**  $(-40^{\circ}\text{C} \le \text{Ta} \le 125^{\circ}\text{C})$ 

Duadinat Nama	-V <sub>DET</sub> [V]			V <sub>HYS</sub> [V]			
Product Name	Min.	Тур.	Max.	Min.	Тур.	Max.	
R5110x01xx	4.518	4.600	4.682	0.046	0.092	0.138	
R5110x02xx	1.572	1.600	1.628	0.016	0.032	0.048	
R5110x03xx	4.419	4.500	4.581	0.045	0.090	0.135	
R5110x04xx	4.321	4.400	4.479	0.044	0.088	0.132	
R5110x05xx	4.223	4.300	4.377	0.043	0.086	0.129	
R5110x06xx	4.125	4.200	4.275	0.042	0.084	0.126	
R5110x07xx	3.634	3.700	3.766	0.037	0.074	0.111	
R5110x08xx	2.946	3.000	3.054	0.030	0.060	0.090	
R5110x09xx	2.848	2.900	2.952	0.029	0.058	0.087	
R5110x10xx	2.750	2.800	2.850	0.028	0.056	0.084	
R5110x11xx	2.652	2.700	2.748	0.027	0.054	0.081	
R5110x12xx	4.027	4.100	4.173	0.041	0.082	0.123	
R5110x13xx	3.045	3.100	3.155	0.031	0.062	0.093	
R5110x142x	4.518	4.600	4.682	0.046	0.092	0.138	

#### **OPERATION DESCRIPTION**

#### **Timing Chart**

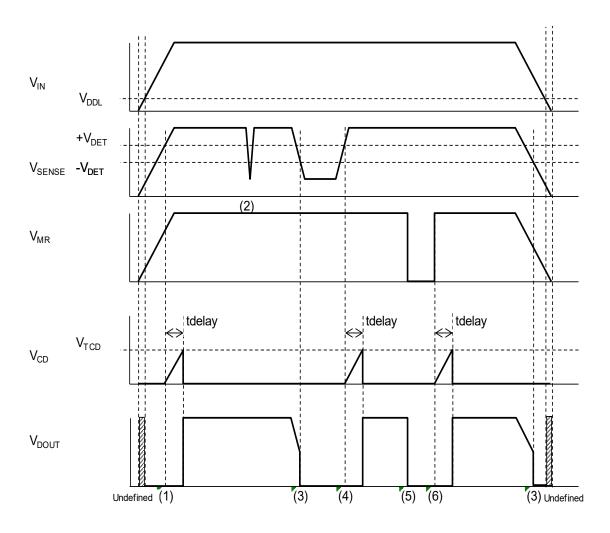
#### R5110Sxx1A / R5110Sxx1B Voltage Detector



R5110Sxx1A / R5110Sxx1B VD Timing Chart

- (1) When the V<sub>OUT</sub> pin voltage (V<sub>OUT</sub>) becomes more than the release voltage (+V<sub>DET</sub>), the RESETB pin voltage (V<sub>RESETB</sub>) becomes "H" after the release output delay time (tdelay).
- (2) When the detect output delay time is less than 30  $\mu$ s (Typ.) even if  $V_{OUT}$  becomes lower than the detector threshold (- $V_{DET}$ ), the voltage detector (VD) does not go into the detecting state.
- (3) When  $V_{\text{OUT}}$  becomes lower than  $-V_{\text{DET}}$ ,  $V_{\text{RESETB}}$  becomes "L" after the detect output delay time (Typ.30 µs) and the VD goes into the detecting state.
- (4) When  $V_{OUT}$  becomes more than  $+V_{DET}$ .  $V_{RESETB}$  becomes "H" after the release output delay time. ( $V_{TCD} = Typ.1 V$ )

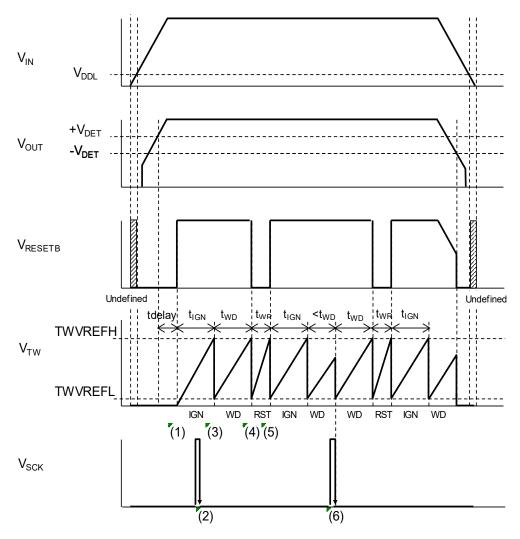
#### R5110xxx2C / R5110xxx2D Voltage Detector



R5110xxx2C / R5110xxx2D VD Timing Chart

- (1) When the SENSE pin voltage (V<sub>SENSE</sub>) becomes more than the release voltage (+V<sub>DET</sub>), the D<sub>OUT</sub> pin voltage (V<sub>DOUT</sub>) becomes "H" after the release output delay time (tdelay).
- (2) When the detect output delay time is 30 μs (Typ.) or less even if V<sub>SENSE</sub> becomes lower than the detector threshold (-V<sub>DET</sub>), the voltage detector (VD) does not go into the detecting state.
- (3) When  $V_{SENSE}$  becomes lower than  $-V_{DET}$ ,  $V_{DOUT}$  becomes "L" after the detect output delay time (Typ. 30  $\mu$ s) and the VD goes into the detecting state.
- (4) When  $V_{SENSE}$  becomes more than  $+V_{DET}$ ,  $V_{DOUT}$  becomes "H" after the release output delay time. ( $V_{TCD} = Typ.1 V$ )
- (5) When the MR pin voltage (V<sub>MR</sub>) becomes "L", V<sub>DOUT</sub> is fixed to "L".
- (6) When V<sub>MR</sub> becomes "L" to "H", V<sub>DOUT</sub> becomes "H" after the release output delay time.

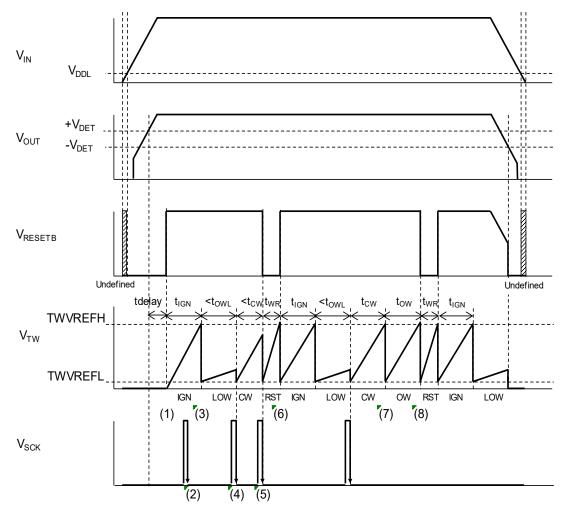
#### R5110Sxx1A Watchdog Timer (Normal Type)



**R5110Sxx1A WDT Timing Chart** 

- (1) When the V<sub>OUT</sub> pin voltage (V<sub>OUT</sub>) becomes more than the release voltage (+V<sub>DET</sub>), the RESETB pin voltage (V<sub>RESETB</sub>) becomes "H" after the release output delay time (tdelay) and the watchdog timer (WDT) starts monitoring a pulse. After that, the TW pin voltage (V<sub>TW</sub>) repeats charge and discharge. As a result, a sawtooth wave is generated. The WDT has three states: Ignoring, Reset, and Monitoring. In each state, the TW pin is charged from 0 V or TWFREFL (Typ.0.08 V).
- (2) After the WDT starts, the WDT is in an ignoring state until V<sub>TW</sub> is charged up to TWVREFH (Typ.2 V). So, a pulse to the SCK pin is ignored during the ignoring state.
- (3) When charging  $V_{TW}$  up to TWVREFH has completed, the TW pin starts discharging and the WDT goes into a monitoring state.
- (4) When a pulse is not sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during the monitoring state, the TW pin starts discharging and the WDT goes into a reset state. During the reset state, V<sub>RESETB</sub> becomes "L.
- (5) When V<sub>TW</sub> is charged up to TWVREFH during the reset state, the TW pin starts discharging and the WDT goes into the ignoring state.
- (6) When a pulse is sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during the monitoring state, the TW pin start discharging and the WDT goes into the next open window state.

#### R5110Sxx1B Watchdog Timer (Window Type)

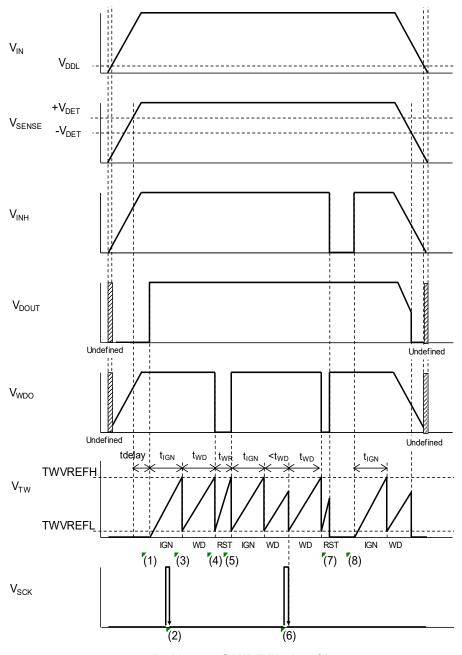


**R5110Sxx1B WDT Timing Chart** 

- (1) When the V<sub>OUT</sub> pin voltage (V<sub>OUT</sub>) becomes more than the release voltage (+V<sub>DET</sub>), the RESETB pin voltage (V<sub>RESETB</sub>) becomes "H" after the release output delay time (tdelaly) and the watchdog timer (WDT) starts monitoring a pulse. After that, the TW pin voltage (V<sub>TW</sub>) repeats charge and discharge. As a result, a sawtooth wave is generated. The WDT has four states: Ignoring, Reset, Open Window, and Closed Window. In each state, the TW pin is charged from 0 V or TWVREFL (Typ.0.08 V).
- (2) After WDT starts, the WDT is in an ignoring state until V<sub>TW</sub> is charged up to TWVREFH (Typ.2 V). So, a pulse to the SCK pin is ignored during the ignoring state.
- (3) When V<sub>Tw</sub> is charged up to TWVREFH during the ignoring state, the TW pin starts discharging and the WDT goes into an open window state. This open window state is four times longer than the normal open window state.
- (4) When a pulse is sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during the open window state, the TW pin starts discharging and the WDT goes into a closed window state.
- (5) When a pulse is sent to the SCK pin before V<sub>TW</sub> reaches TWVREF during the closed window state, the TW pin starts discharging and the WDT goes into a reset state. During the reset state, V<sub>RESETB</sub> becomes "L".

- (6) When V<sub>TW</sub> reaches TWVREFH during the reset state, the TW pin starts discharging and the WDT goes into the ignoring state.
- (7) When a pulse is not sent to the SCK pin before  $V_{TW}$  reaches TWVREFH during the closed window state, the TW pin starts discharging and the WDT goes into the open window state.
- (8) When a pulse is not sent to the SCK pin before  $V_{TW}$  reaches TWVREFH during the open window state, the TW pin starts discharging and the WDT goes into the reset state.

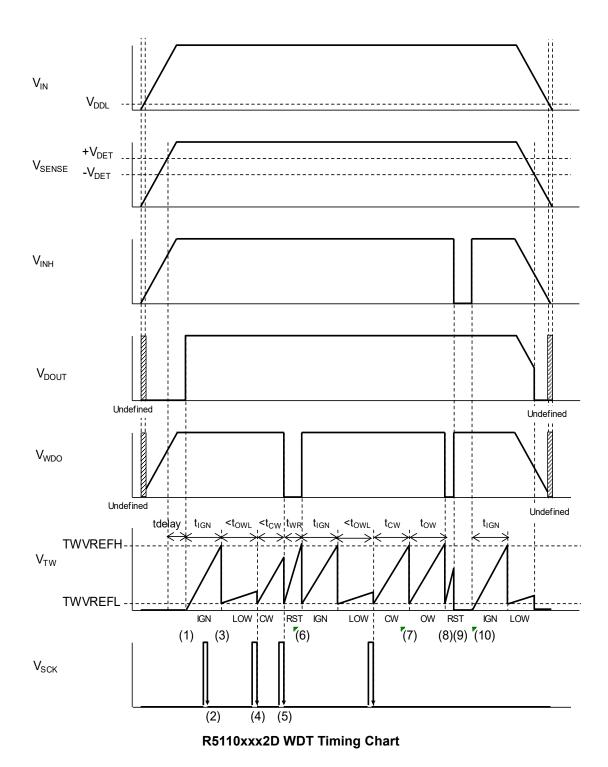
## R5110xxx2C Watchdog Timer (Normal Type)



R5110xxx2C WDT Timing Chart

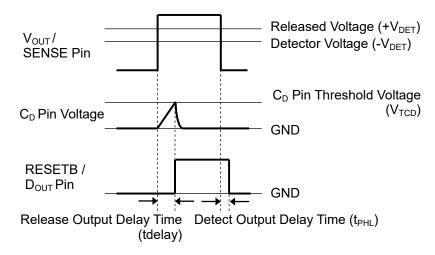
- (1) When the SENSE pin voltage (V<sub>SENSE</sub>) becomes more than the release voltage (+V<sub>DET</sub>), the D<sub>OUT</sub> pin voltage (V<sub>DOUT</sub>) becomes "H" after the release output delay time (tdelay) and the watchdog timer (WDT) starts monitoring a pulse. After that, the TW pin voltage (V<sub>TW</sub>) repeats charge and discharge. As a result, a sawtooth wave is generated. The WDT has three states: Ignoring, Reset, and Monitoring. In each state, the TW pin is charged from 0 V or TWVREFL (Typ.0.08 V).
- (2) After the WDT starts, the WDT is in an ignoring state until  $V_{TW}$  is charged up to TWVREFH. So, a pulse to the SCK pin is ignored during the ignoring state.
- (3) When  $V_{TW}$  is charged up to TWVREFH during the ignoring state, the TW pin starts discharging and the WDT goes into a monitoring state.
- (4) When a pulse is not sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during the monitoring state, the TW pin starts discharging and the WDT goes into a reset state. During the reset state, the WDO pin voltage (V<sub>WDO</sub>) becomes "L".
- (5) When V<sub>TW</sub> reaches TWVREFH during the reset state, the TW pin starts discharging and the WDT goes into an ignoring state.
- (6) When a pulse is sent to the SCK pin before  $V_{TW}$  reaches TWVREFH during the monitoring, the TW pin starts discharging and the WDT goes into the next monitoring state.
- (7) The WDT stops monitoring by setting the INH pin voltage (V<sub>INH</sub>) to "L". Then, V<sub>WDO</sub> is fixed to "H" and V<sub>TW</sub> is fixed to "L".
- (8) When changed V<sub>INH</sub> from "L" to "H", the WDT goes into the ignoring state and restarts monitoring.

#### R5110xxx2D Watchdog Timer (Window Type)



- (1) When the SENSE pin voltage (V<sub>SENSE</sub>) becomes more than the release voltage (+V<sub>DET</sub>), the D<sub>OUT</sub> pin voltage (V<sub>DOUT</sub>) becomes "H" after the release output delay time (tdelay) and the watchdog timer (WDT) starts monitoring a pulse. After that, the TW pin voltage (V<sub>TW</sub>) repeats charge and discharge. As a result, a sawtooth wave is generated. The WDT has four states: Ignoring, Reset, Open Window, and Closed Window. In each state, the TW pin is charged from 0 V or TWVREFL (Typ.0.08 V).
- (2) After WDT starts, the WDT is in an ignoring state until  $V_{TW}$  is charged up to TWVREFH. So, a pulse to the SCK pin is ignored during the ignoring state.
- (3) When V<sub>TW</sub> is charged up to TWVREFH during the ignoring state, the TW pin starts discharging and the WDT goes into an open window state. This open window state is four times longer than the normal open window state.
- (4) When a pulse is sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during the open window state, the TW pin starts discharging and the WDT goes into a closed window state.
- (5) When a pulse is sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during the close window state, the TW pin starts discharging and the WDT goes into a reset state. During the reset state, V<sub>DOUT</sub> becomes "L".
- (6) When V<sub>TW</sub> reaches TWVREFH during the reset state, the TW pin starts discharging and the WDT goes into an ignoring state.
- (7) When a pulse is not sent to the SCK pin before V<sub>TW</sub> reaches TWVREFH during a closed window state, the TW pin starts discharging and the WDT goes into an open window state.
- (8) When a pulse is not sent to the SCK pin before  $V_{TW}$  reaches TWVREFH during the open window state, the TW pin starts discharging and the WDT goes into a reset state.
- (9) The WDT stops monitoring by setting the INH pin voltage (V<sub>INH</sub>) to "L". Then, V<sub>WDO</sub> is fixed to "H" and V<sub>TW</sub> is fixed to "L".
- (10) When changed V<sub>INH</sub> from "L" to "H". the WDT goes into the ignoring state and restarts monitoring.

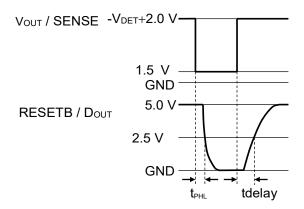
#### **Delay Operation and Released Output Delay Time (tdelay)**



**Released Output Delay Timing Diagram** 

When the operating voltage higher than the released voltage is applied to VOUT pin (R5110Sxx1A/R5110Sxx1B) or SENSE pin (R5110xxx2C/R5110xxx2D), charge to an external capacitor starts, then CD pin voltage (VCD) increases. RESETB pin (R5110Sxx1A/R5110Sxx1B) or DOUT pin (R5110xxx2C/R5110xxx2D) maintains the released output until VCD reaches the threshold voltage of the release output delay pin (VTCD). And when VCD is over VTCD, RESETB pin or DOUT pin is inverted from "L" to "H". That is, the charged external capacitor starts discharging.

When the operating voltage lower than the detector threshold is applied to VDD pin, the detect output delay time, which is the time until the output voltage is inverted from "H" to "L", remains constant independent of the external capacitor.



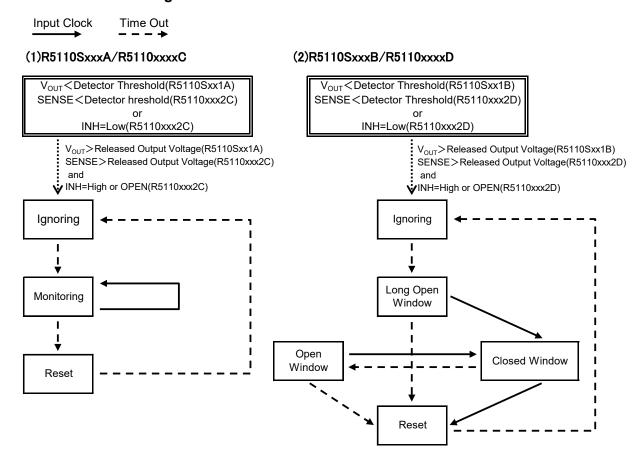
**Released Output Delay Time** 

Released Output Delay Time (tdelay) indicates the time between the instance when  $V_{OUT}$  pin (R5110Sxx1A / R5110Sxx1B) or SENSE pin (R5110xxx2C / R5110xxx2D) shifts from "1.5 V" to "- $V_{DET}$  + 2.0 V" by the application of a pulse voltage and the instance when the output voltage reaches 2.5 V after pulled up RESETB pin (R5110Sxx1A / R5110Sxx1B) or  $D_{OUT}$  pin (R5110xxx2C/ R5110xxx2D) to 5.0 V with a resistor of 100 k $\Omega$ . This is given by the expression tdelay (s) = 1.1 ×  $C_D$  (F) / (1.0×10<sup>-6</sup>), where  $C_D$  (F) represents capacitance of

the external capacitor.

If  $V_{OUT}$  / SENSE pin goes up at a mild pace of 0.1V/s or less, connect a capacitor of 100 pF or more to  $C_D$  pin.

#### **WDT State Transition Diagram**



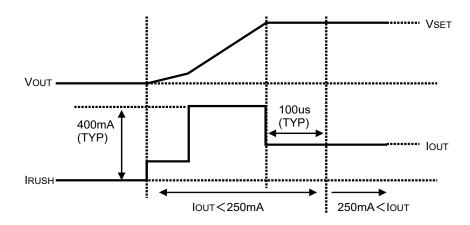
## **Time Setting for Watchdog Timer**

The following time of WDT is dependent on a capacitor connecting to the TW pin. Relationship between the value of capacitor and time can be expressed by the following equations.

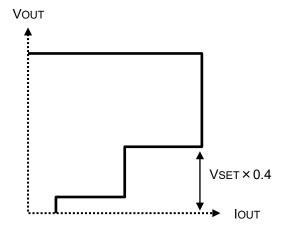
$$\begin{split} &T_{OW}(s) = 1.8 \times C(F) \, / \, (1.0 \times 10^{-6}) \\ &t_{CW}(s) = 1.8 \times C(F) \, / \, (1.0 \times 10^{-6}) \\ &t_{OWL}(s) = 1.8 \times C(F) \, / \, (0.25 \times 10^{-6}) \\ &t_{IGN}(s) = 1.8 \times C(F) \, / \, (1.0 \times 10^{-6}) \\ &t_{WD}(s) = 1.8 \times C(F) \, / \, (1.0 \times 10^{-6}) \\ &t_{WR}(s) = 1.9 \times C(F) \, / \, (2.0 \times 10^{-6}) \end{split}$$

#### **Inrush Current Prevention at Rising Characteristics**

R5110x has the inrush current preventing circuit to control the inrush current within about 400mA limited. This circuit works during the rising periods. Therefore, the load current must be increased after rising up the output voltage (at typ.100 µs after being out of the inrush current limited condition) by the sequence control. When the load current is increased during the rising periods, the inrush current must be controlled within 250 mA.



Likewise, on the thermal shutdown and the foldback characteristic, the inrush current preventing circuit works when the output voltage re-rises after the output voltage fall down to a guideline ( $V_{SET} \times 0.4$ ) or less.



#### **Standby Function**

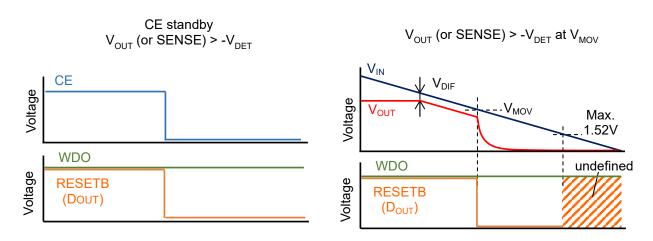
When CE turns to low, the R5110x goes into the standby mode. During this mode, the voltage regulator (VR) stops the output, the watchdog timer (WDT) stops the pulse monitoring, and the voltage detector (VD) stops the voltage monitoring.

Even if  $V_{IN}$  < 3.5 V (Minimum Operating Voltage  $V_{MOV}$ ), VR stops the output, WDT stops the pulse monitoring, and VD stops the voltage monitoring. When CE = low or  $V_{IN}$  < 3.5 V (Minimum Operating Voltage), the output of WDT and VD become as follows regardless of SENSE voltage.

R5110Sxx1A/ R5110Sxx1B: The RESETB output is fixed to "L".

R5110xxx2C/ R5110xxx2D: The D<sub>OUT</sub> is fixed to "L", and WDO output is fixed to the pull-up voltage.

When  $V_{IN}$  is under 1.52 V, values of RESETB output (R5110Sxx1A/ R5110Sxx1B) and  $D_{OUT}$  output (R5110xxx2C/ R5110xxx2D) become indefinite, 0.1 V or more (pull-up voltage 5 V, pull-up resistance 100 k $\Omega$ ).



#### Voltage Setting (R5110Sxx1A / R5110Sxx1B)

VD detects the drop of the VR output voltage ( $V_{OUT}$ ). When the VD release voltage ( $+V_{DET}$ ) is set to a voltage above the VR output voltage, the reset signal of VD is not released even if VD monitors the VR output voltage returns to the normal value after detecting the drop of VR. To prevent this issue, the following condition is required between  $V_{OUT}$  and  $+V_{DET}$ .

(VR Set Output Voltage) x 0.985 – 30 mV > (VD Set Detector Threshold) x 1.018 x 1.030

When using a device with the above conditions of  $V_{OUT}$  and  $+V_{DET}$ , careful consideration must be given to the system operation before use.

#### Manual Reset (MR) Function (R5110xxx2C, R5110xxx2D)

Setting the MR pin to "L" forcefully sets  $D_{OUT}$  to "L". The maximum value of the delay time ( $t_{MR}$ ), which is until  $D_{OUT}$  outputs "L", is 1 $\mu$ s as an index of the performance. The MR pin is pulled-up by an internal resistor (Typ.110 $k\Omega$ ). Current is passed to the MR pin when the voltage of MR >  $V_{DD}$ . But, this current has no effect to the operation because the current is limited with a pull-up resistor.

When setting the MR pin from "L" to "H", D<sub>OUT</sub> is changed from "L" to "H" after the released output delay time and the WDT starts from the ignoring state.

When the MR pin is "L", the WDO pin outputs "H".

#### SENSE Function (R5110xxx2C, R5110xxx2D)

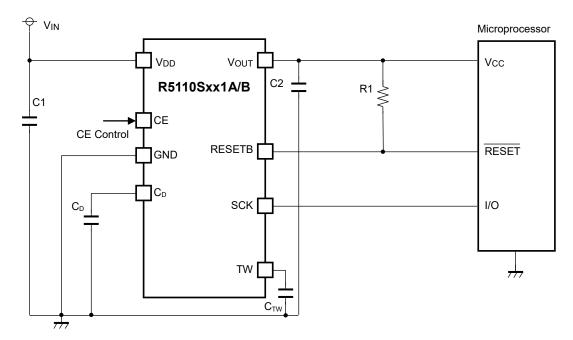
The internal voltage detector monitors the input voltage to the SENSE pin. To measure the proper detector threshold, setting of  $V_{IN} \ge 3.5 \text{ V}$  is required.

#### Inhibition (INH) Function (R5110xxx2C, R5110xxx2D)

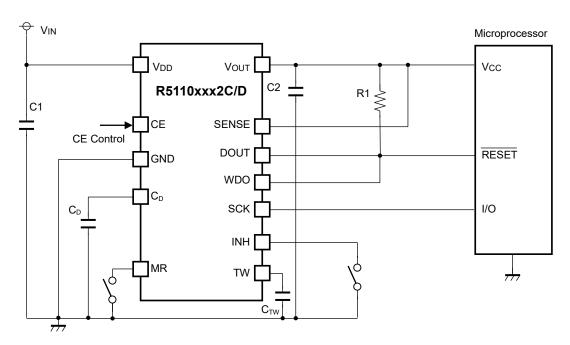
Setting the INH pin to "L" stops the WDT pulse monitoring function and the WDO pin is fixed to "H". The INH pin is pulled up with an internal resistor (Typ.110  $k\Omega$ ).

# **APPLICATION INFORMATION**

# **Typical Application Circuits**



R5110Sxx1A/B Typical Application



R5110xxx2C/D Typical Application

#### **External Components**

Symbol	Description
C1 (C <sub>IN</sub> )	0.1 μF, Ceramic Capacitor
C2 (C <sub>OUT</sub> )	0.1 μF, Ceramic Capacitor
Стw	A capacitor corresponding to time setting for Watchdog Timer is required.  Refer to "Time Setting for WDT" in Operation Description for details.
C <sub>D</sub>	A capacitor corresponding to setting for Release Output Delay Time is required. Refer to "Delay Operation and Release Output Delay Time (tdelay)" in Operation Description for details.
R1	A resistor is required to set with consideration of the output current and the leakage current. Refer to "Electrical Characteristic" for details.

#### **TECHNICAL NOTES**

#### **Phase Compensation**

In the Ics, phase compensation is made for securing stable operation even if the load current is varied. For this purpose, use a capacitor C2 with 0.1  $\mu$ F or more.

If a tantalum capacitor is used, and its ESR (Equivalent Series Resistance) of C2 is large, the loop oscillation may result. Because of this, select C2 carefully considering its frequency characteristics.

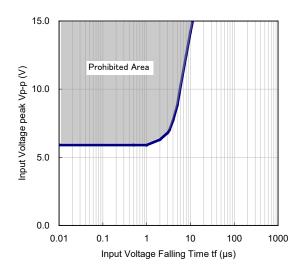
#### **PCB Layout**

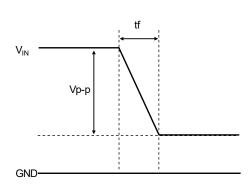
Make  $V_{DD}$  and GND lines sufficient. If their impedance is too high, noise pickup or unstable operation may result. Connect 0.1  $\mu$ F or more of the capacitor C1 between the  $V_{DD}$  and GND, and as close as possible to the pins.

In addition, connect the capacitor C2 between V<sub>OUT</sub> and GND, and as close as possible to the pins.

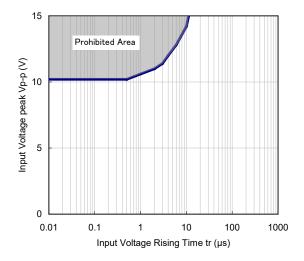
## **Prohibited Area for Fluctuations in Input Voltage**

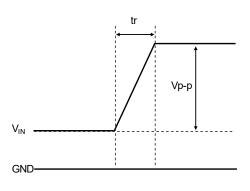
Please take note that miss-detection or miss-release might be invited when changing an input voltage abruptly in the following prohibited area.





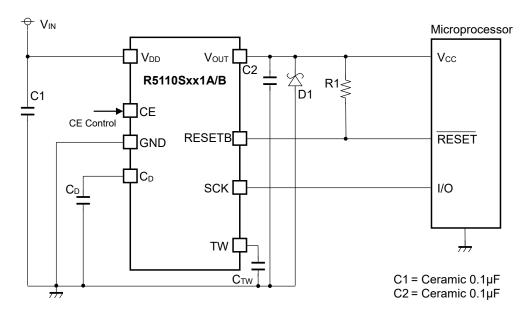
Prohibited Area of Fluctuation at Falling of VIN





Prohibited Area of Fluctuation at Rising of  $V_{\text{IN}}$ 

#### Typical Application for IC Chip Breakdown Prevention



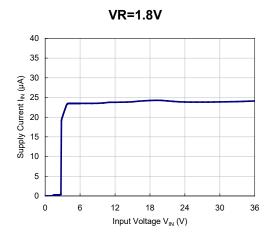
**R5110Sxxxx Typical Application** 

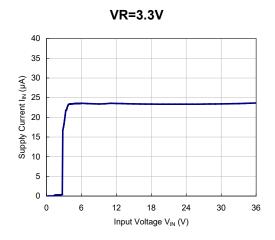
When a sudden surge of electrical current travels along the VOUT pin and GND due to a short-circuit, electrical resonance of a circuit involving an output capacitor (C2) and a short circuit inductor generates a negative voltage and may damage the device or the load devices. Connecting a schottky diode (D1) between the VOUT pin and GND has the effect of preventing damage to them.

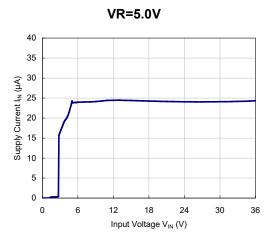
# **TYPICAL CHARACTERISTICS**

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

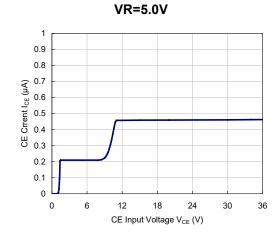
#### 1) Power Consumption vs. Input Voltage (Ta = 25°C)



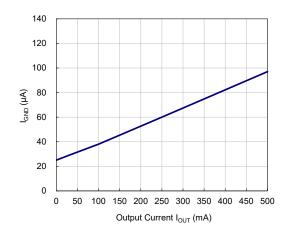




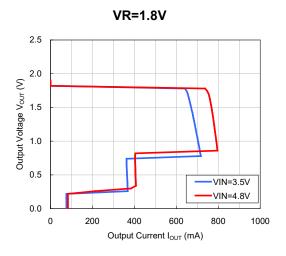
## 2) CE Pin Current vs. CE Pin Voltage (Ta = 25°C, V<sub>IN</sub>=14V)

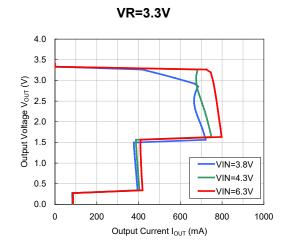


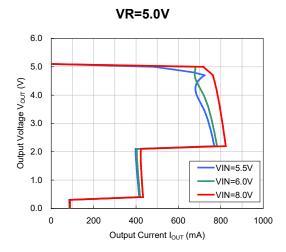
## 3) GND Pin Current vs. Output Current (Ta = 25°C)



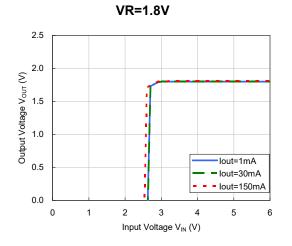
#### 4) Output Voltage vs. Output Current (Ta = 25°C)

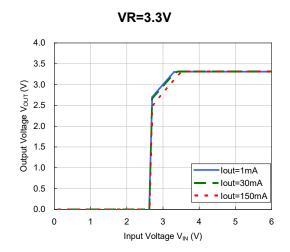


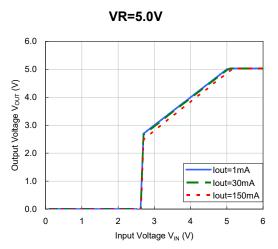




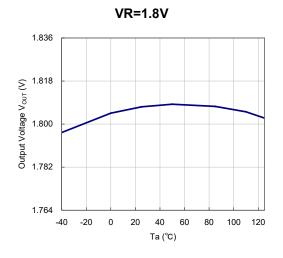
# 5) Output Voltage vs. Input Voltage (Ta = 25°C)

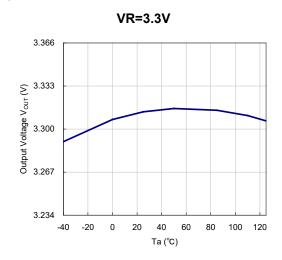


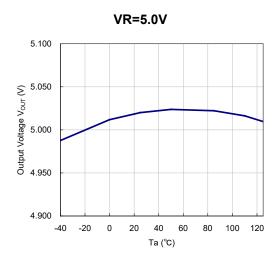




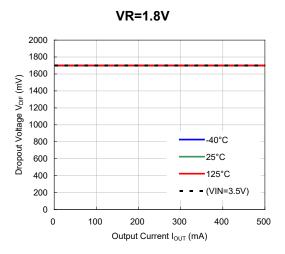
# 6) Output Voltage vs. Temperature (V<sub>IN</sub>=14V, I<sub>OUT</sub>=1mA)

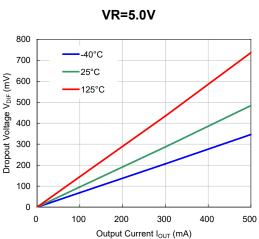


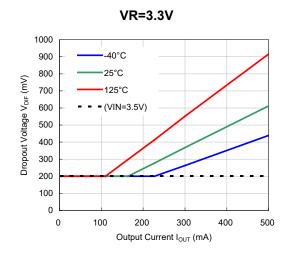




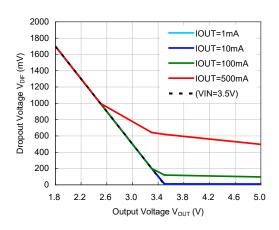
# 7) Dropout Voltage vs. Output Current





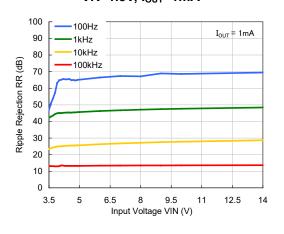


# 8) Dropout Voltage vs. Output Voltage (Ta=25°C)

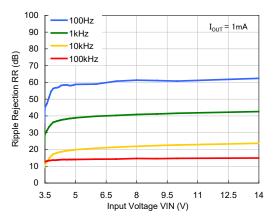


# 9) Ripple Rejection vs. Input Voltage (Ta=25°C, Ripple = 0.2 Vpp)

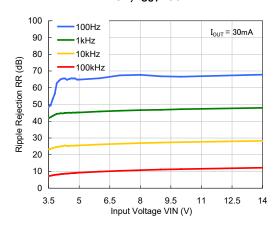
VR=1.8V, I<sub>OUT</sub>=1mA



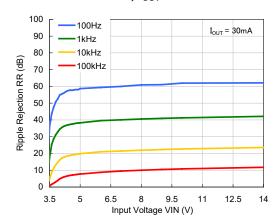
VR=3.3V,  $I_{OUT}$ =1mA

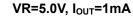


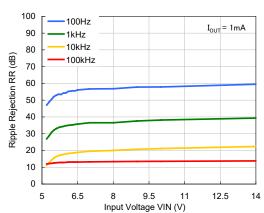
VR=1.8V, I<sub>OUT</sub>=30mA



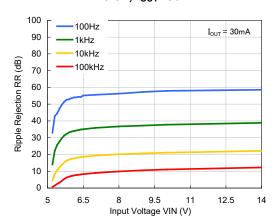
VR=3.3V,  $I_{OUT}$ =30mA



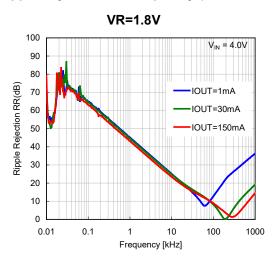


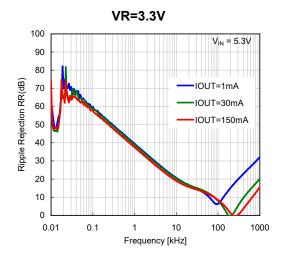


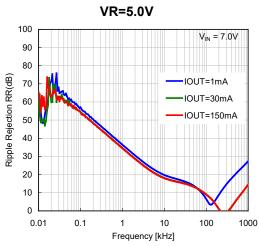
# VR=5.0V, I<sub>OUT</sub>=30mA



# 10) Ripple Rejection vs. Frequency (Ta=25°C, Ripple=0.2 Vpp)

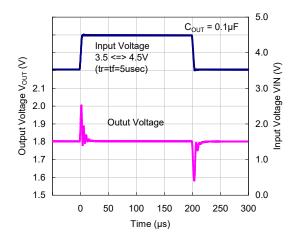




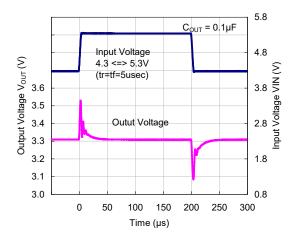


## 11) Input Transient Respon (Ta=25°C)

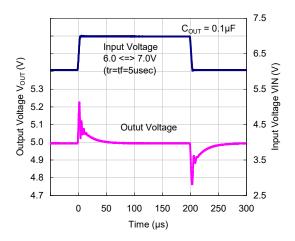
VR=1.8V,  $I_{OUT}$ =30mA,  $C_{OUT}$ =0.1 $\mu$ F



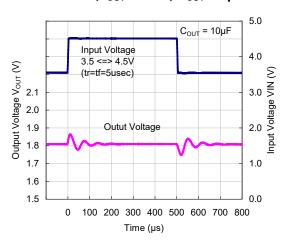
VR=3.3V,  $I_{OUT}$ =30mA,  $C_{OUT}$ =0.1 $\mu$ F



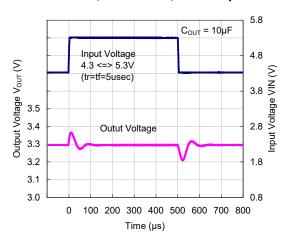
VR=5.0V, I<sub>OUT</sub>=30mA, C<sub>OUT</sub>=0.1μF



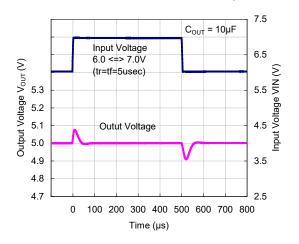
VR=1.8V, I<sub>OUT</sub>=30mA, C<sub>OUT</sub>=10µF



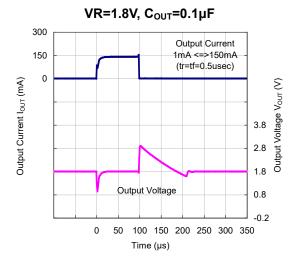
VR=3.3V,  $I_{OUT}$ =30mA,  $C_{OUT}$ =10 $\mu$ F

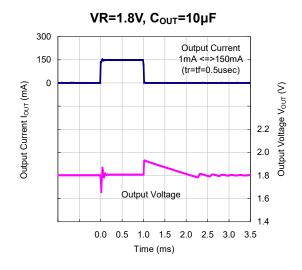


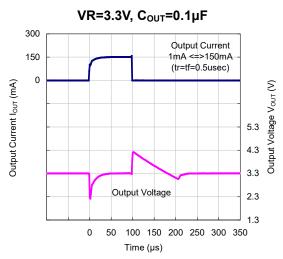
VR=5.0V, I<sub>OUT</sub>=30mA, C<sub>OUT</sub>=10µF

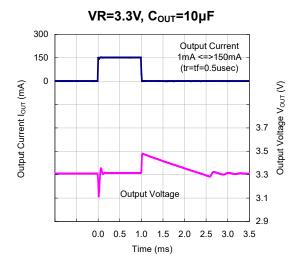


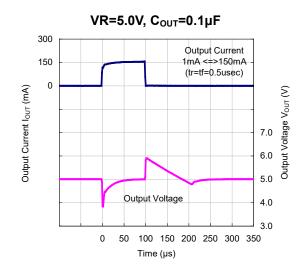
## 12) Load Transient Response (Ta=25°C)

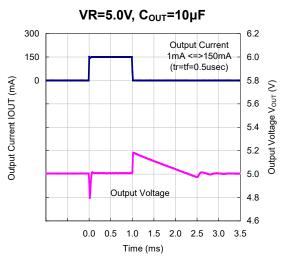




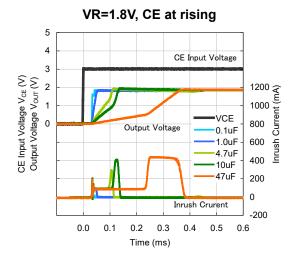


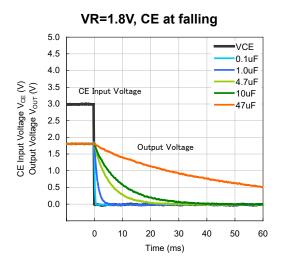


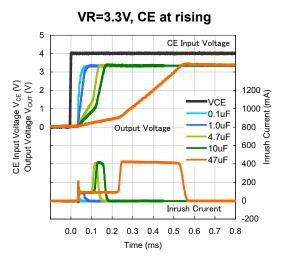


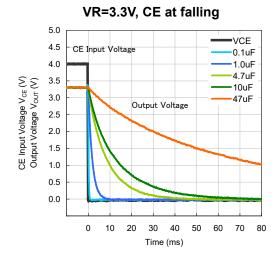


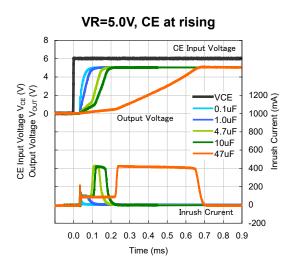
# 13) CE Transient Response (Ta=25°C, $V_{IN}$ =14V, $I_{OUT}$ =1mA, $C_{OUT}$ =0.1 $\mu$ ~47 $\mu$ F)

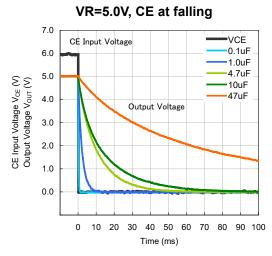




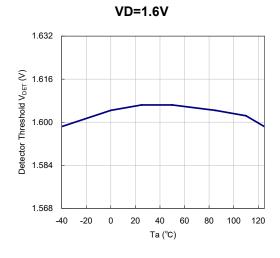


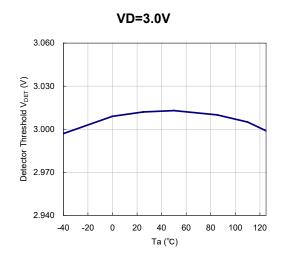


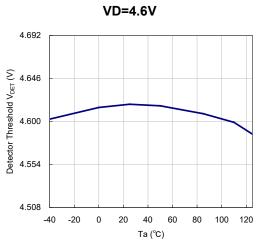




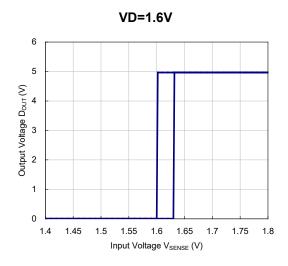
# 14) Detector Threshold vs. Temperature

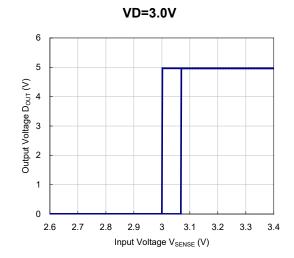


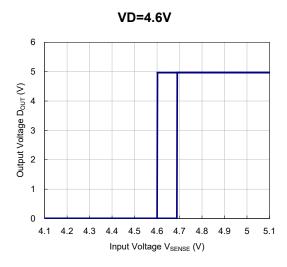




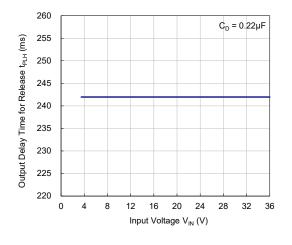
# 15) $D_{OUT}$ Pin Voltage vs. SENSE Pin Input Voltage ( $D_{OUT}$ pulled-up to 5V with $100k\Omega$ )



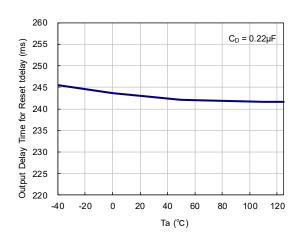




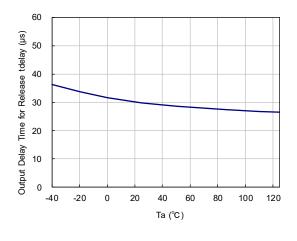
# 16) Release Output Delay Time vs. Input Voltage



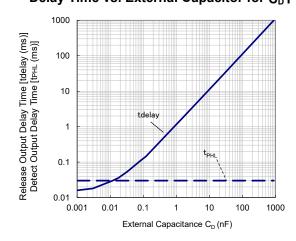
# 17) Release Output Delay Time vs. Temperature



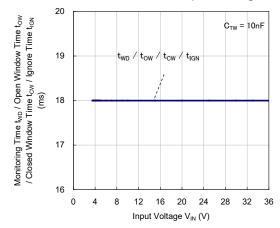
# 17) Detect Output Delay Time vs. Temperature



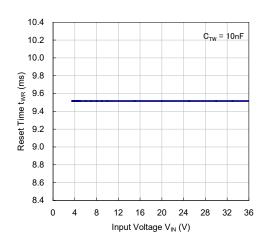
# 19) Release Output Delay Time and Detect Output Delay Time vs. External Capacitor for C<sub>D</sub> Pin



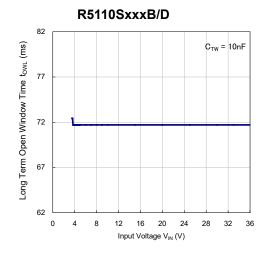
# 20) WDT $t_{WD}$ / $t_{OW}$ / $t_{CW}$ / $t_{IGN}$ vs. Input Voltage



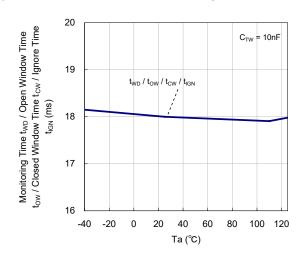
# 21) Reset Time vs. Input Voltage



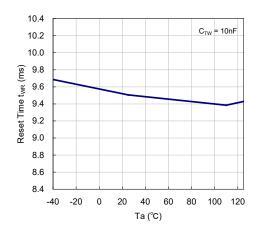
# 22) Long Open Window Time vs. Input Voltage



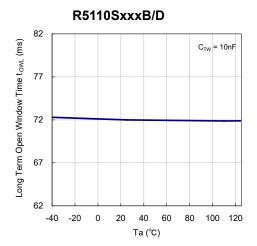
# 23) WDT $t_{\text{WD}} / \; t_{\text{OW}} / \; t_{\text{CW}} / \; t_{\text{IGN}} \, \text{vs.}$ Temperature



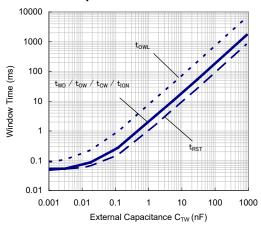
#### 24) Reset Time vs. Temperature



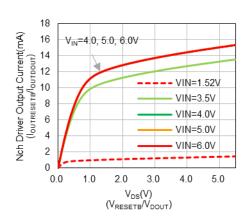
#### 25) Long Open Window Time vs. Temperature



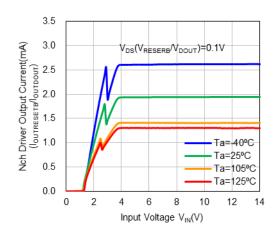
26) WDT twD / tow / tcw / tign /towL / trst Vs. External Capacitor for C<sub>TW</sub> Pin



# 27) Nch. Driver Output Current vs. V<sub>DS</sub>

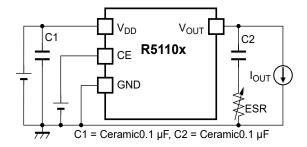


#### 28) Nch. Driver Output Current vs. Input Voltage



# **ESR vs. Output Current**

The IC is recommended to use a ceramic type capacitor, but the IC can be used other capacitors of the lower ESR type. The relation between the output current ( $I_{OUT}$ ) and the ESR of output capacitor is shown below.



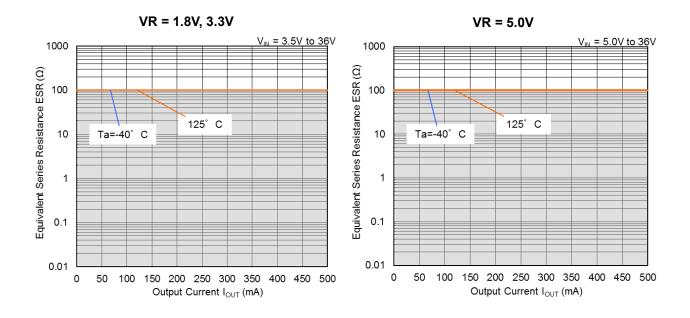
#### **Measurement conditions:**

Frequency Band: 10 Hz to 2 MHz

Measurement Temperature: -40°C to 125°C

Hatched area: Noise level is 40 µV (average) or below

Ceramic Capacitor: C1 = C2 = Ceramic 0.1 µF



PD-HSOP-8E-(125150)-JE-B

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

#### **Measurement Conditions**

Item	Measurement Conditions
Environment	Mounting on Board (Wind Velocity = 0 m/s)
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square
Through-holes	φ 0.3 mm × 21 pcs

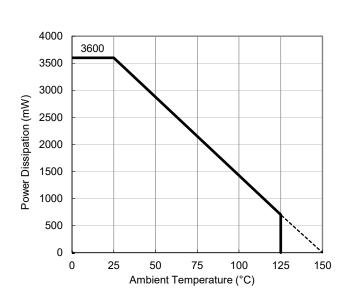
#### **Measurement Result**

(Ta = 25°C, Tjmax = 150°C)

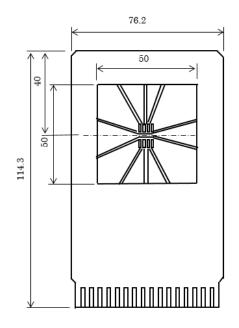
Item	Measurement Result		
Power Dissipation	3600 mW		
Thermal Resistance (θja)	θja = 34.5°C/W		
Thermal Characterization Parameter (ψjt)	ψjt = 10°C/W		

θja: Junction-to-Ambient Thermal Resistance

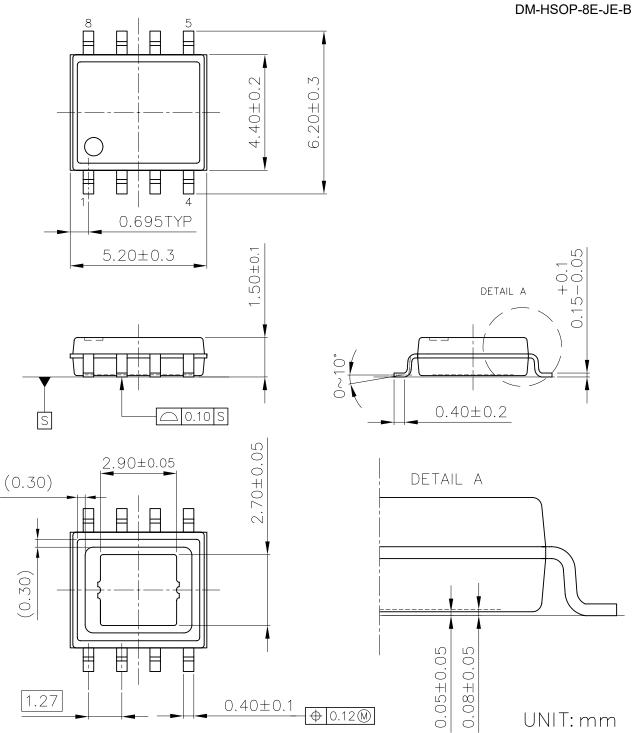
ψjt: Junction-to-Top Thermal Characterization Parameter



Power Dissipation vs. Ambient Temperature



**Measurement Board Pattern** 

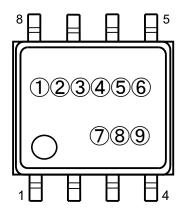


**HSOP-8E Package Dimensions** 

MK-R5110S-(HSOP-8E)-JE-A

023456: Product Code  $\cdots$  Refer to Part Marking List

⑦ ⑧ ⑨: Lot Number · · · Alphanumeric Serial Number



R5110S (HSOP-8E) Part Markings

# NOTICE

There can be variation in the marking when different AOI (Automated Optical Inspection) equipment is used. In the case of recognizing the marking characteristic with AOI, please contact our sales or our distributor before attempting to use AOI.

R5110Sxx1A/B Part Marking List

Product Name	①②③④⑤⑥ Product Nam	Draduat Nama	023456	V <sub>SET</sub> / -V <sub>SET</sub>	
		Product Name		VR	VD
R5110S011A	R S 0 0 7 A	R5110S011B	R S 0 0 7 N	5.0V	4.6V
R5110S021A	R S 0 0 7 B	R5110S021B	R S 0 0 7 P	1.8V	1.6V
R5110S031A	R S 0 0 7 C	R5110S031B	R S 0 0 7 R	5.0V	4.5V
R5110S041A	R S 0 0 7 D	R5110S041B	R S 0 0 7 S	5.0V	4.4V
R5110S051A	R S 0 0 7 E	R5110S051B	R S 0 0 7 T	5.0V	4.3V
R5110S061A	R S 0 0 7 F	R5110S061B	R S 0 0 7 U	5.0V	4.2V
R5110S071A	R S 0 0 7 G	R5110S071B	R S 0 0 7 V	5.0V	3.7V
R5110S081A	R S 0 0 7 H	R5110S081B	R S 0 0 7 W	3.3V	3.0V
R5110S091A	R S 0 0 7 J	R5110S091B	R S 0 0 7 X	3.3V	2.9V
R5110S101A	R S 0 0 7 K	R5110S101B	R S 0 0 7 Y	3.3V	2.8V
R5110S111A	R S 0 0 7 L	R5110S111B	R S 0 0 7 Z	3.3V	2.7V
R5110S121A	R S 0 0 7 M	R5110S121B	R S 0 0 8 A	5.0V	4.1V
R5110S131A	R S 0 0 8 B	R5110S131B	R S 0 0 8 C	3.4V	3.1V

PD-HSOP-18-(125150)-JE-B

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

#### **Measurement Conditions**

Item	Measurement Conditions
Environment	Mounting on Board (Wind Velocity = 0 m/s)
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square
Through-holes	φ 0.3 mm × 21 pcs

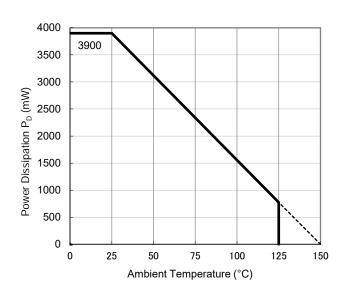
#### **Measurement Result**

(Ta = 25°C, Tjmax = 150°C)

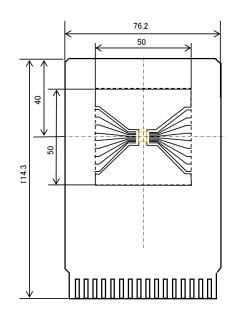
Item	Measurement Result	
Power Dissipation	3900 mW	
Thermal Resistance (θja)	θja = 32°C/W	
Thermal Characterization Parameter (ψjt)	ψjt = 8°C/W	

θja: Junction-to-Ambient Thermal Resistance

ψjt: Junction-to-Top Thermal Characterization Parameter

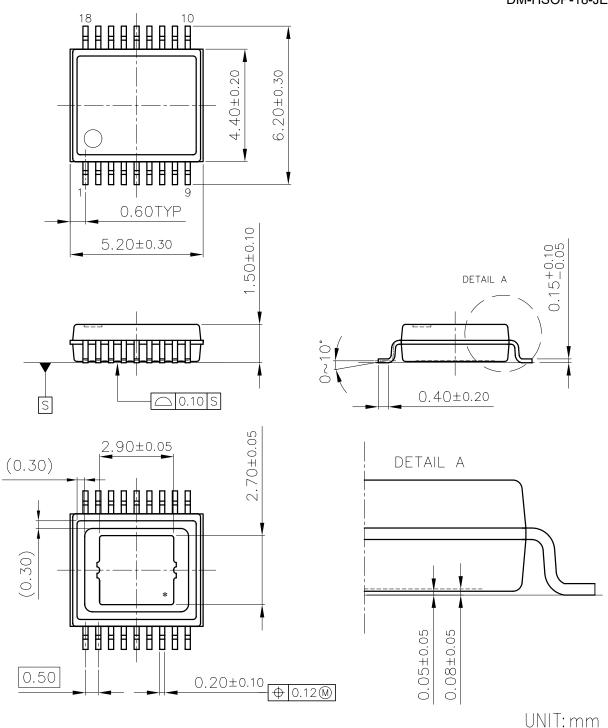


Power Dissipation vs. Ambient Temperature



**Measurement Board Pattern** 

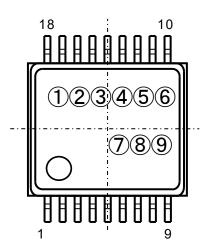
DM-HSOP-18-JE-B



**HSOP-18 Package Dimensions** 

MK-R5110S-(HSOP-18)-JE-B

 $\textcircled{1} \textcircled{2} \textcircled{3} \textcircled{4} \textcircled{5} \textcircled{6} \text{: Product Code } \cdots \text{ Refer to } \textit{Part Marking List}$ 



R5110S (HSOP-18) Part Markings

#### NOTICE

There can be variation in the marking when different AOI (Automated Optical Inspection) equipment is used. In the case of recognizing the marking characteristic with AOI, please contact our sales or our distributor before attempting to use AOI.

R5110Sxx2C/D Part Marking List

Product Name	①②③④⑤⑥ Product Name	Due de et Nome		V <sub>SET</sub> / -V <sub>SET</sub>	
		023456	VR	VD	
R5110S012C	R S 1 0 2 A	R5110S012D	R S 1 0 2 N	5.0V	4.6V
R5110S022C	R S 1 0 2 B	R5110S022D	R S 1 0 2 P	1.8V	1.6V
R5110S032C	R S 1 0 2 C	R5110S032D	R S 1 0 2 R	5.0V	4.5V
R5110S042C	R S 1 0 2 D	R5110S042D	R S 1 0 2 S	5.0V	4.4V
R5110S052C	R S 1 0 2 E	R5110S052D	R S 1 0 2 T	5.0V	4.3V
R5110S062C	R S 1 0 2 F	R5110S062D	R S 1 0 2 U	5.0V	4.2V
R5110S072C	R S 1 0 2 G	R5110S072D	R S 1 0 2 V	5.0V	3.7V
R5110S082C	R S 1 0 2 H	R5110S082D	R S 1 0 2 W	3.3V	3.0V
R5110S092C	R S 1 0 2 J	R5110S092D	R S 1 0 2 X	3.3V	2.9V
R5110S102C	R S 1 0 2 K	R5110S102D	R S 1 0 2 Y	3.3V	2.8V
R5110S112C	R S 1 0 2 L	R5110S112D	R S 1 0 2 Z	3.3V	2.7V
R5110S122C	R S 1 0 2 M	R5110S122D	R S 1 0 3 A	5.0V	4.1V
R5110S132C	R S 1 0 3 B	R5110S132D	R S 1 0 3 C	3.4V	3.1V
R5110S142C	R S 1 0 3 D	R5110S142D	R S 1 0 3 E	3.3V	4.6V

# Nisshinbo Micro Devices Inc.

PD-HQFN0808-28-(125150)-JE-A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

#### **Measurement Conditions**

Item	Measurement Conditions		
Environment	Mounting on Board (Wind Velocity = 0 m/s)		
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)		
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm		
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square		
Through-holes	φ 0.3 mm × 72 pcs		

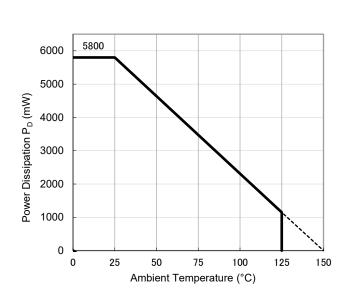
#### **Measurement Result**

 $(Ta = 25^{\circ}C, Tjmax = 150^{\circ}C)$ 

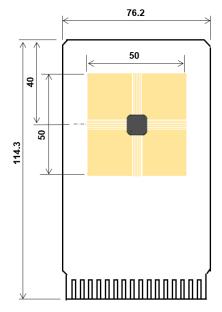
Item	Measurement Result		
Power Dissipation	5800 mW		
Thermal Resistance (θja)	θja = 21.5°C/W		
Thermal Characterization Parameter (ψjt)	ψjt = 5°C/W		

 $\theta$ ja: Junction-to-ambient thermal resistance.

ψjt: Junction-to-top of package thermal characterization parameter

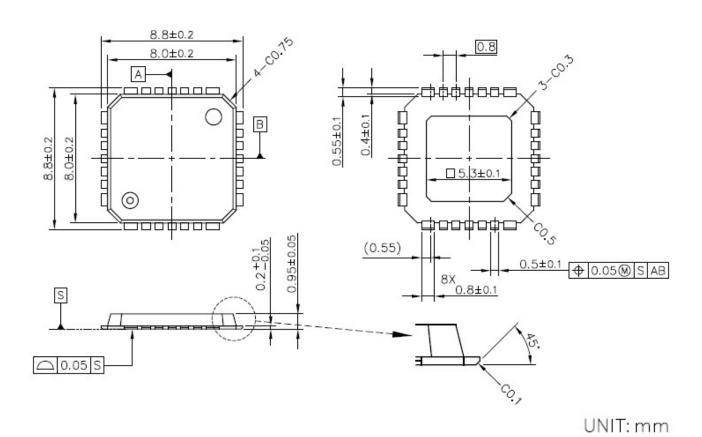


**Power Dissipation vs. Ambient Temperature** 



**Measurement Board Pattern** 

DM-HQFN0808-28-JE-A



**HQFN0808-28 Package Dimensions** 

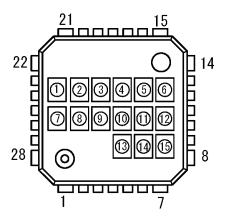
Nisshinbo Micro Devices Inc.

PART MARKINGS R5110L

MK-R5110L-JE-A

①~⑩: Product Code ··· Refer to Part Marking List

 $\textcircled{1}\sim \textcircled{5}$ : Lot Number  $\cdots$  Alphanumeric Serial Number



R5110L (HQFN0808-28) Part Markings

# NOTICE

There can be variation in the marking when different AOI (Automated Optical Inspection) equipment is used. In the case of recognizing the marking characteristic with AOI, please contact our sales or our distributor before attempting to use AOI.

R5110LxxxC/D Part Marking List

Draduat Nama	oduct Name ① to ⑩	Product Name	① to ⑩	V <sub>SET</sub> / -V <sub>SET</sub>	
Product Name				VR	VD
R5110L012C	R5110L012C	R5110L012D	R5110L012D	5.0V	4.6V
R5110L022C	R5110L022C	R5110L022D	R5110L022D	1.8V	1.6V
R5110L032C	R5110L032C	R5110L032D	R5110L032D	5.0V	4.5V
R5110L042C	R5110L042C	R5110L042D	R5110L042D	5.0V	4.4V
R5110L052C	R5110L052C	R5110L052D	R5110L052D	5.0V	4.3V
R5110L062C	R5110L062C	R5110L062D	R5110L062D	5.0V	4.2V
R5110L072C	R5110L072C	R5110L072D	R5110L072D	5.0V	3.7V
R5110L082C	R5110L082C	R5110L082D	R5110L082D	3.3V	3.0V
R5110L092C	R5110L092C	R5110L092D	R5110L092D	3.3V	2.9V
R5110L102C	R5110L102C	R5110L102D	R5110L102D	3.3V	2.8V
R5110L112C	R5110L112C	R5110L112D	R5110L112D	3.3V	2.7V
R5110L122C	R5110L122C	R5110L122D	R5110L122D	5.0V	4.1V
R5110L132C	R5110L132C	R5110L132D	R5110L132D	3.4V	3.1V
R5110L142C	R5110L142C	R5110L142D	R5110L142D	3.3V	4.6V

# Nisshinbo Micro Devices Inc.

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  - Power Generator Control Equipment (nuclear, steam, hydraulic, etc.)
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  - Vehicle Control Equipment (airplane, railroad, ship, etc.)
  - Various Safety Devices
  - Traffic control system
  - Combustion equipment

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- 6. We are making our continuous effort to improve the quality and reliability of our products, but semiconductor products are likely to fail with certain probability. In order to prevent any injury to persons or damages to property resulting from such failure, customers should be careful enough to incorporate safety measures in their design, such as redundancy feature, fire containment feature and fail-safe feature. We do not assume any liability or responsibility for any loss or damage arising from misuse or inappropriate use of the products.
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- 8. Quality Warranty
  - 8-1. Quality Warranty Period

In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.

8-2. Quality Warranty Remedies

When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.

Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.

8-3. Remedies after Quality Warranty Period

With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.

- 9. Anti-radiation design is not implemented in the products described in this document.
- 10. The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
- 11. WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
- 12. Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
- 13. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.



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